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In the Specification:

Please amend the specification as follows.

Please amend paragraph [0074] on page 29 of the specification as follows:

[0074] In another embodiment according to the present invention, a lamination process is substituted for the spin coating process in order to deposit the high conductivity inducing polymer in step 1115. Suitable lamination processes for this purpose are disclosed in U.S. patent application Ser. No. 10/949,632[[ ]], which claimed priority to Provisional U.S. Patent Application Ser. No. 60/505,880 filed concurrently herewith and ~~herewith,~~ entitled "Process for Laminating a Dielectric Layer onto ~~into~~ a Semiconductor," the former of which issued on January 24, 2006 as U.S. Patent No. 6,989,336. ~~Semiconductor."~~ This patent ~~application~~ is assigned to E. I. du Pont de Nemours and Company, ~~docket No. CL-2181,~~ and is hereby incorporated herein by reference in its entirety. It is to be understood that such lamination processes can be used in substitution for spin coating processes in all of the instances where spin coating is discussed in this specification.

Please amend paragraph [0111] on page 41 of the specification as follows:

[0111] FIGS. 11-16 as discussed above relate to exemplary and non limiting embodiments of methods according to the present invention. Other suitable methods for making the exemplary devices shown in FIGS. 1-10 can also be used. For example, other processes can be used for

providing the high and low conductivity inducing polymer layers and regions on the insulating substrates. Such other processes can include, for example, ink jet printing, vapor deposition, liquid film casting, spin casting, evaporative film casting, and thermal transfer imaging. High and low conductivity inducing polymer layers can be patterned, for example, by photolithography and oxygen plasma etching. Continuous coatings can be converted into defined layer regions by laser ablation, for example. Further processes that may be useful in making the exemplary devices shown in FIGS. 1-10 are disclosed in U.S. patent application Ser. No. 10/669,780[[ ]], filed concurrently herewith, entitled "Semiconductor Layers with Roughness Patterning", which issued on November 29, 2005 as U.S. Patent No. 6,969,634. This patent is assigned to Lucent Technologies Inc., and is ~~the entirety of which is~~ hereby incorporated by reference herein in its entirety.

Please amend paragraph [0113] bridging pages 42 and 43 of the specification as follows:

[0113] A laser head is provided adjacent to the printer cylinder, aimed to direct laser light onto the cylinder surface through the assembled films. The laser head may, for example, include 200 lasers having a collective beam width of 500 microns, providing a resolution of 2 x 5 microns. The exemplary laser spot size has a length of 5 microns across the head, and a width of 2 microns in the direction of printer cylinder rotation. The laser head includes a lead screw for guiding the laser head over the longitudinal axis of the printer cylinder. In operation of the printer, the cylinder turns at a selected rotation rate per unit time, and the lead screw systematically advances the laser head over the printer cylinder surface in a barber pole fashion. The lasers within the

laser head can be individually energized for precise pattern control. As the laser head is guided over the surface of the printer cylinder, laser light is directed in a precise desired pattern corresponding to the desired high or low conductivity inducing polymer layers or regions on the insulating substrate. Typically, the precise pattern is computer generated. In the precise areas where laser energy enters the donor film, the high or low conductivity inducing polymer is transferred onto the insulating substrate. Fine accuracy of the printing pattern is needed. This accuracy can be achieved by proper programming of the computer guidance systems. Further advantageous embodiments of laser induced thermal transfer imaging processes that can be employed in practice of various aspects of the present invention are disclosed in U.S. patent application Ser. No. 10/949,867[[_____]],which claimed priority to Provisional U.S. Patent Application Ser. No. 60/505,533 filed concurrently herewith, entitled "Method for Increasing Mobility of Vapor Deposited Pentacene." This patent application is assigned to E. I. du Pont de Nemours and Company, docket No. CL-2447, and is hereby incorporated by reference herein in its entirety.